



TERA21 System Key Specifications Summary

TERA21 System Key Specifications	
Model Name	PSK TERA21 300mm Ashing System
Wafer Size	300mm (12 inch)
Process Type	Plasma Ashing / Dry Etching / Photoresist Stripping
Process Chamber	2 x Twin Chamber (Standard 2, Expandable to 3) Process 2 wafers simultaneously per chamber
Plasma Source	Downstream Microwave Source - 4 x MKS Astex FI20160-1 Microwave Generator - 4 x MKS RPS System - 4 x ENI-NOVA-25A RF Power Supply
Robot System	• EFEM: ATM RORZE (RA7L018) Robot • TM: NIDEC SANKYO 4-Paddle Robot • MASIC (Multi Axis Synchronized Interpolation Control)
Loadport	3 x RORZE (RV201) FOUP Loadport
Throughput	High Productivity (2x vs Single Chamber due to Twin Chamber)
Key Process Functions	• FEOL Photoresist Strip • PR Removal after High Dose Implant • ISBP (In-Situ Bake Process) - Popping Free Solution • Isotropic Etching, Descum Process
Gas System	• O₂, N₂, AR, CF₄, CHF₃, HE • MFC Precision Control • Automatic Gas Supply & Monitoring
Pressure Control	• Capacitance Manometer • Vacuum Gauge & Isolation Valve • FSM/Emerson Pressure Control System
Wafer Tracing	OCR & Aligner Included (Smart In-Line Wafer Trace System)
Process Features	• Low Damage • High Selectivity Control • Excellent Process Uniformity • Low CoO (Cost of Ownership)